SiSA72ADN Vishay Siliconix

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Vish

N-Channel 40 V (D-S) MOSFET



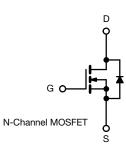
PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.00342
$R_{DS(on)}$ max. (Ω) at V_{GS} = 4.5 V	0.00466
Q _g typ. (nC)	14.8
I _D (A)	92
Configuration	Single

FEATURES

- TrenchFET[®] Gen IV power MOSFET
- Tuned for the lowest R_{DS}-Q_{oss} FOM
- 100 % R_q and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Synchronous rectification
- High power density DC/DC
- DC/AC inverters
- Battery and load switch



ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSA72ADN-T1-GE3

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DS}	40	N	
Gate-source voltage		V _{GS}	+20, -16	
	T _C = 25 °C		92	
Continuous drain surrent (T 150 °C)	T _C = 70 °C		74	
Continuous drain current ($T_J = 150 \ ^\circ C$)	T _A = 25 °C	I _D	24.8 ^{b, c}	
	T _A = 70 °C		19.8 ^{b, c}	
Pulsed drain current (t = 100 µs)	I _{DM}	150	- A	
Ocation of a sum of the sum of the sum of the	T _C = 25 °C		47.2	
Continuous source-drain diode current	T _A = 25 °C	I _S	3.3 ^{a, b}	
Single pulse avalanche current		I _{AS}	15	
Single pulse avalanche Energy	L = 0.1 mH	E _{AS}	11.25	mJ
	T _C = 25 °C		52	
Manimum manual aliania atian	T _C = 70 °C		33.3	
Maximum power dissipation	T _A = 25 °C	P _D	3.7 ^{a, b}	— W
	T _A = 70 °C		2.4 ^{a, b}	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	•••
Soldering recommendations (peak temperature		260		

THERMAL RESISTANCE RATINGS SYMBOL PARAMETER TYPICAL MAXIMUM UNIT Maximum junction-to-ambient b, f $t \le 10 \ s$ R_{thJA} 24 33 °C/W Maximum junction-to-case (drain) Steady state R_{thJC} 1.9 2.4

Notes

a. T_C = 25 °C

b. Surface mounted on 1" x 1" FR4 board

c. t = 10 s

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

f. Maximum under steady state conditions is 81 °C/W

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HALOGEN

FREE

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			•				
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$		-	-	V	
V _{DS} temperature coefficient			-	22	-		
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-5.4	-	mV/°C	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	1	-	2.4	V	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +20, -16 V	-	-	± 100	nA	
7		$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1		
Zero gate voltage drain current	IDSS	$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$	-	-	10	μA	
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 V$, $V_{GS} = 10 V$	30	-	-	А	
		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$			0.00342	0	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	0.00388	0.00466	Ω	
Forward transconductance ^a	g _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	76	-	S	
Dynamic ^b			•	•			
Input capacitance	C _{iss}		-	2530	-		
Output capacitance	C _{oss}		-	465	-	pF	
Reverse transfer capacitance	C _{rss}	$V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz$	-	19	-		
C _{rss} /C _{iss} ratio			-	0.0075	0.0150		
	Q _g	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 26 \text{ A}$	-	33	50	nC	
Total gate charge			-	14.8	23		
Gate-source charge	Q _{gs}	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 26 \text{ A}$	-	8.2	-		
Gate-drain charge	Q _{gd}		-	2.3	-		
Output charge	Q _{oss}	$V_{DS} = 20 V, V_{GS} = 0 V$	-	17.6	27		
Gate resistance	Rg	f = 1 MHz	0.26	1.3	2.6	Ω	
Turn-on delay time	t _{d(on)}		-	15	30		
Rise time	tr	$V_{DD} = 20 V, R_I = 1 \Omega$	-	7	14	-	
Turn-off delay time	t _{d(off)}	$I_D \cong 20.8 \text{ Å}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	35	70		
Fall time	t _f		-	5	10		
Turn-on delay time	t _{d(on)}		-	30	60	ns	
Rise time	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{\text{I}} = 1 \Omega$	-	150	300	-	
Turn-off delay time	t _{d(off)}	$I_D \cong 20.8 \text{ Å}, V_{GEN} = 4.5 \text{ V}, \text{ R}_g = 1 \Omega$	-	35	70		
Fall time	t _f	-		14	28		
Drain-Source Body Diode Characteristic	s			•			
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	47.2		
Pulse diode forward current ($t_p = 100 \ \mu s$) I_{SM}		-	-	-	150	A	
Body diode voltage	V _{SD}	I _S = 10 A	-	0.74	1.1	V	
Body diode reverse recovery time	t _{rr}	5	-	22	44	ns	
Body diode reverse recovery charge	Q _{rr}	I _F = 20.8 A, di/dt = 100 A/μs,	-	10	20	nC	
Reverse recovery Fall time	t _a	$T_{\rm J} = 25 ^{\circ}{\rm C}$	-	12	-	-	
Reverse recovery rise time	t _b			10	_	ns	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

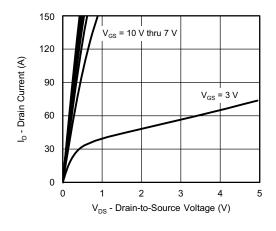
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

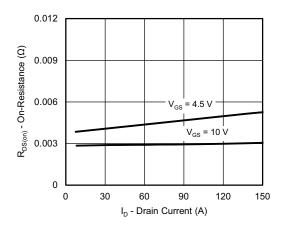
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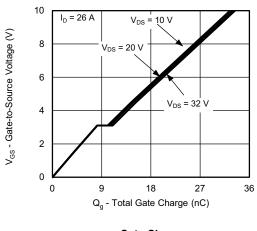
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



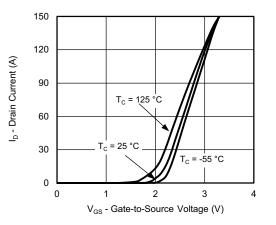
Output Characteristics



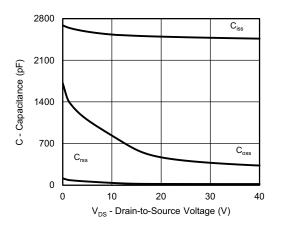
On-Resistance vs. Drain Current



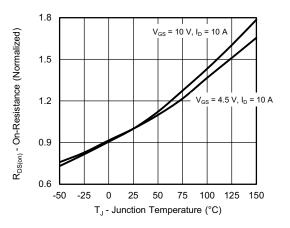
Gate Charge



Transfer Characteristics



Capacitance



On-Resistance vs. Junction Temperature

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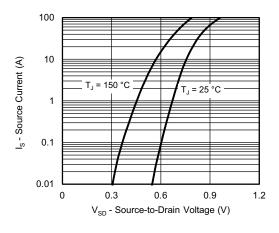
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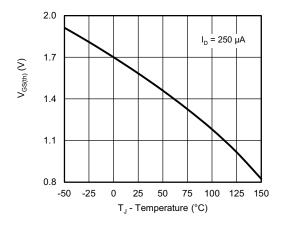
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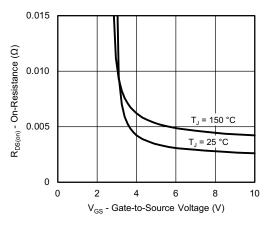
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



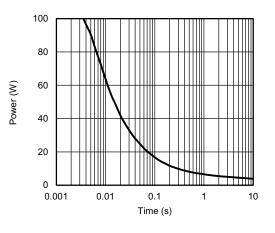
Source-Drain Diode Forward Voltage



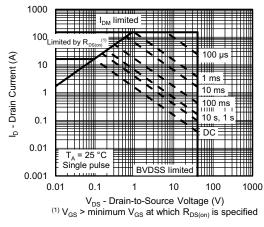
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



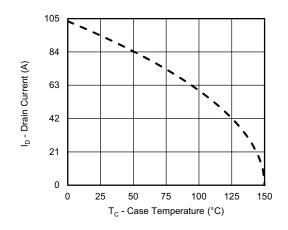
Safe Operating Area

4

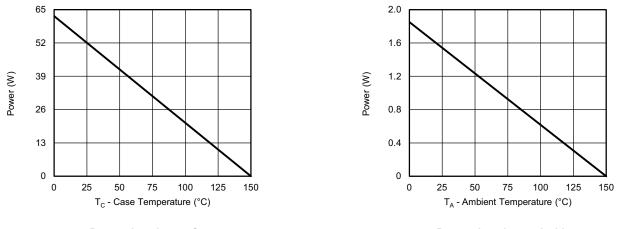
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



Power, Junction-to-Case

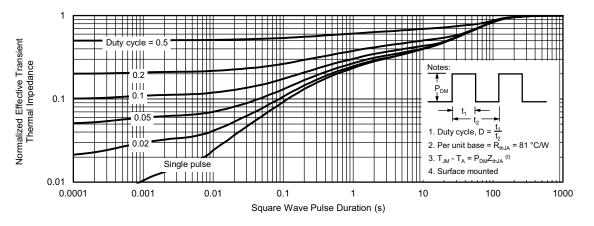
Power, Junction-to-Ambient

Note

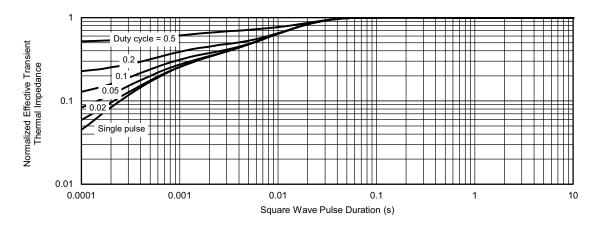
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

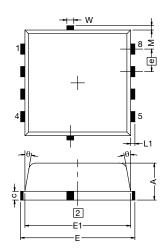


Normalized Thermal Transient Impedance, Junction-to-Case

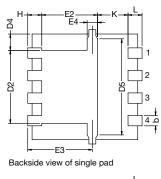
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PowerPAK® 1212-8, (Single / Dual)









Notes

1. Inch will govern

Dimensions exclusive of mold gate burrs
Dimensions exclusive of mold flash and cutting burrs

DIM.	MILLIMETERS			INCHES			
DINI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0.00	-	0.05	0.000	-	0.002	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D3	0.48	-	0.89	0.019	-	0.035	
D4		0.47 typ.		0.0185 typ			
D5		2.3 typ.		0.090 typ			
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4	0.034 typ.			0.013 typ.			
е		0.65 BSC		0.026 BSC			
К	0.86 typ.			0.034 typ.			
K1	0.35	-	-	0.014	-	-	
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.			0.005 typ.			
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Revison: 09-Jan-17

Document Number: 71656

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RECOMMENDED MINIMUM PADS FOR PowerPAK[®] 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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